L Number	Hits	Search Text	DB	Time stamp
1	60	(semiconductor near laser) and faces and (cavity near3 length) and (QW or (quantum near well)) and (reflect$6 near2 low$3) and (reflect$6 near2 higH)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 12:48
-	768	(semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (mirror or ((low and high) near reflect$)) and 372/$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/14 16:26
-	260	((semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (mirror or ((low and high) near reflect$)) and 372/$) and 372/96	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/29 18:04
-	11	(((semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (mirror or ((low and high) near reflect$)) and 372/$) and 372/96) and (laminat$ near structure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/29 18:05
-	4	(semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and ((low and high) near reflect$) and 372/$ and (laminat$ near structure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/14 16:28
-	4	((semiconductor near laser) and (active near (layer or region or medium or film) SAME (quantum near well or qw)) and ((low and high) near reflect$) and (laminat$ near structure)) and 372/$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/29 18:19
-	5	(semiconductor near laser) and (active near (layer or region or medium or film) SAME (quantum near well or qw)) and ((low and high) near reflect$) and (laminat$ near structure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/29 19:24
-	73	(semiconductor near laser) and (active near (layer or region or medium or film) SAME (quantum near well or qw)) and ((low and high) near reflect$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/29 19:27
-	1	(semiconductor near laser) and (active near (layer or region or medium or film) SAME (quantum near well or qw)) and ((low and high) near mirror) and (laminat$ near structure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/29 19:27
-	56	((semiconductor near laser) and (active near (layer or region or medium or film) SAME (quantum near well or qw)) and ((low and high) near reflect$)) and 372/$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/29 19:28
-	4	(semiconductor near laser) and (active near (layer or region or medium or film) SAME (quantum near well or qw)) and ((low and high) near mirror)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/29 19:42

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-	1093	(semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (mirror or ((low and high) near reflect$)) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/14 16:36
-	186	(semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect$5)and (high near reflect$5) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/14 16:48
-	113	((semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect$5)and (high near reflect$5) and substrate) and cavity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/14 17:25
-	63	((semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect$5)and (high near reflect$5) and substrate) and (cavity near2 length)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/14 17:26
-	43	((semiconductor near laser) with (optical near fiber)) and (active near (layer or region or medium or film)) and (quantum near well or qw) and ((low and high) near reflect$) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/16 15:26
-	4	(("4651322") or ("4731792") or ("5870417") or ("5337291")).PN.	USPAT	2003/01/12 13:07
-	1	("5377291").PN.	USPAT	2003/01/12 13:14
-	0	(semiconductor near laser) and faces and cavity and (QW or (quantum near weel)) and (reflection near2 (low or hihg))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/12 13:15
-	193	(semiconductor near laser) and faces and cavity and (QW or (quantum near weLl)) and (reflect$6 near2 (low or higH))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/12 13:18
-	173	((semiconductor near laser) and faces and cavity and (QW or (quantum near weLl)) and (reflect$6 near2 (low or higH))) AND (active near (medium or region or film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/12 13:18
-	131	(semiconductor near laser) and faces and cavity and ((active near (medium or region or film or layer)) with (QW or (quantum near weLl))) and (reflect$6 near2 (low or higH))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/12 13:33
-	54	(semiconductor near laser) and faces and (cavity near3 length) and ((active near (medium or region or film or layer)) with (QW or (quantum near well))) and (reflect$6 near2 (low or higH))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/12 13:39
-	33	(semiconductor near laser) and faces and (cavity near3 length) and ((active near (medium or region or film or layer)) with (QW or (quantum near well))) and (reflect$6 near2 (low$3)) and (reflect$6 near2 (hig$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/12 14:19
-	0	2001/0048702	US-PGPUB	2003/01/12 14:19
-	0	Yohida.in.	US-PGPUB	2003/01/12 14:19

	0	Yohida		US-PGPUB	2003/01/12 14:20
-	1106	Yoshida.in.		US-PGPUB	2003/01/12 14:21

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